

*AL 1*

4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl, an accelerant selected from the group consisting of organic phosphites, organic borates and water, and mixtures thereof, and a source of oxygen.

*AL 2*

Claim 5. (Amended Twice) The process of claim 1 where said composition is gaseous at a temperature below about 175°C.

*AL 3*

Claim 23. (Amended Twice) A process for forming an oxide composition comprising oxidizing a [gaseous] composition which is gaseous at a temperature below about 200°C at atmospheric pressure, and which is adapted to deposit at least a first amorphous layer comprising tin oxide and silicon oxide onto glass at a rate of deposition greater than about 400 Å/sec., the layer having a controlled index of refraction, wherein the composition comprises a tin oxide precursor, a silicon oxide precursor of formula  $R_mO_nSi_p$ , where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl, and at least one accelerant chosen from the group consisting of boron and phosphorous esters and water.

*AL 4*

Claim 25. (Amended Twice) A process for forming an oxide composition comprising oxidizing a [gaseous] composition which is gaseous at a temperature below about 200°C and at atmospheric pressure, and which is adapted to deposit at least a

first layer comprising amorphous tin oxide and silicon oxide onto glass at a temperature of from about 450° to 650°C at a rate of deposition greater than about 350 Å/sec. wherein the composition comprises:

a tin oxide precursor of formula  $R_nSnX_{4-n}$ , where R is a straight, cyclic, or branched-chain alkyl, or alkenyl of from one or about six carbons; phenyl, substituted phenyl, or  $R'CH_2CH_2-$ , where R' is  $MeO_2C-$ ,  $EtO_2C-$ ,  $CH_3CO-$ , or  $HO_2C-$ ; X is selected from the group consisting of halogen, acetate, perfluoroacetate, and their mixtures; and where n is 0, 1, or 2;

a silicon oxide precursor of formula  $R_mO_nSi_p$ , where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl;

one or more accelerants selected from the group consisting of water and organic phosphites and organic borates of formula  $(R''O)_3P$  and  $(R''O)_3B$  where R'' is independently chosen from straight, cyclic or branched-chain alkyl or alkyl of from one to about six carbons; phenyl, substituted phenyl, or  $R'''CH_2CH_2-$ , where R''' is  $MeO_2C-$ ,  $EtO_2C-$ ,  $CH_3CO-$ , or  $HOOC-$ ; and a source of oxygen.

Claim 28. (Amended Twice) A process for forming an oxide composition comprising oxidizing a gaseous composition comprising at least one precursor of a metal oxide and an accelerant selected from the group consisting of organic

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